

80V N-Channel Power MOSFET

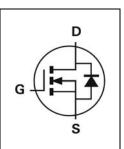
V_{DSS}, 80V

 $R_{\text{DS(ON)}}$, $8.0 m\Omega$ (max.) @ $V_{\text{GS}}\text{=}10 V$

 I_D , 84A



DC-DC converters and Off-line UPS



Description	Features
The SG75N07PB uses advanced Trench technology and designs to provide excellent R _{DS(ON)} with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	 Low On-Resistance Low Input Capacitance Low Miller Charge Low Input / Output Leakage Pb-free lead plating; RoHS compliant
	Applications
	Motor / Body Load ControlLoad Switch

Ordering Information

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG75N07PB	Halogen-Free	TO-220AB-D	PB	Tube	50

Absolute Maximum Ratings (T_A=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V _{DS}	80	V
Gate-Source Voltage		V _{GS}	±25	V
Desire Comment Continuous	T _C =25°C		84	А
Drain Current-Continuous	T _C =100°C	ID I	53	А
Drain Current-Pulsed Note 1		I _{DM}	300	Α
Avalanche Current, L=0.1mH		las	53	А
Avalanche Energy, L=0.1mH		Eas	400	mJ
Maximum Dawar Dissination	T _C =25°C	D	86.8	W
Maximum Power Dissipation	T _C =100°C	P _D	34.7	W
Operating Junction Temperature Range		T _J T _{STG}	-55 to +150	°C

Thermal Resistance Ratings

Hornia Roolotano Ratingo						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient Note 2	R _{θJA}	Steady State	-	-	62	°C/W
Maximum Junction-to-Case Note 2	Rejc	Steady State	-	-	1.44	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _{DS} =250µA	80	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage	Igss	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _{DS} =250µA	2	3	4	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _{DS} =30A	-	-	8.0	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	4936	-	
Output Capacitance	Coss	V _{DS} =30V, V _{GS} =0V, f=1MHz	-	251	-	pF
Reverse Transfer Capacitance	C _{rss}		-	107	1	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T _{d(on)}		-	25	-	
Rise Time	tr	V _{DD} =30V, I _D =30A, V _{Gs} =10V,	-	21	-]
Turn-Off Delay Time	$T_{d(off)}$	Rg=3Ω	-	85	-	ns
Fall Time	tf		-	42	-	
Total Gate Charge at 10V	Qg		-	84	-	
Gate to Source Gate Charge	Q _{gs}	V _{DS} =30V, I _{DS} =30A, V _{GS} =10V	-	24	-	nC
Gate to Drain "Miller" Charge	Q _{gd}		-	25	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =30A	-	-	1.3	V
Body Diode Reverse Recovery Time	t _{rr}	1 -204 -41/44-4004/	-	32	-	ns
Body Diode Reverse Recovery Charge	Qrr	l _F =30A, dl/dt=100A/μs	-	47	-	nC

Notes:

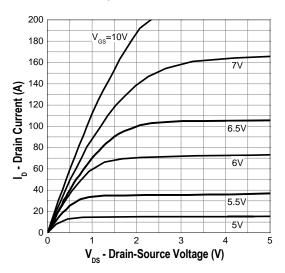
- 1. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 2. Reja is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Reja is guaranteed by design while Reca is determined by the user's board design. Reja shown below for single device operation on FR-4 in still air.



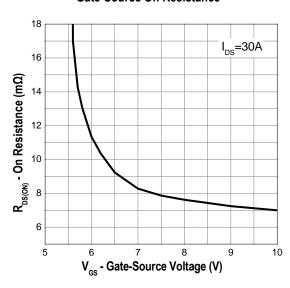
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Typical Operating Characteristics

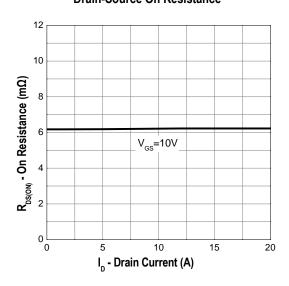
Output Characteristics



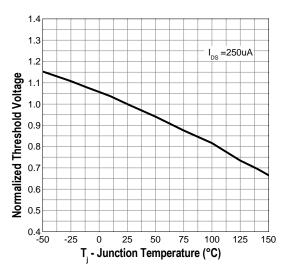
Gate-Source On Resistance



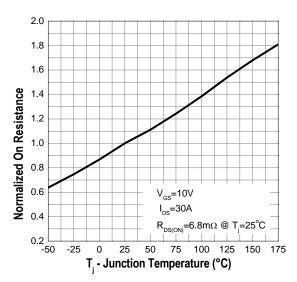
Drain-Source On Resistance



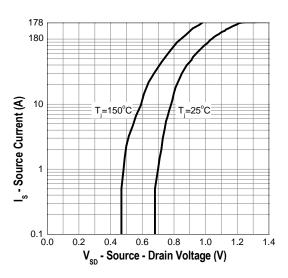
Gate Threshold Voltage



Drain-Source On Resistance



Source-Drain Diode Forward

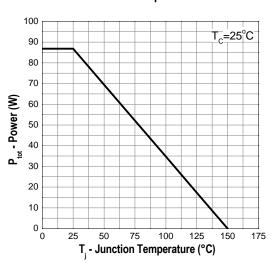




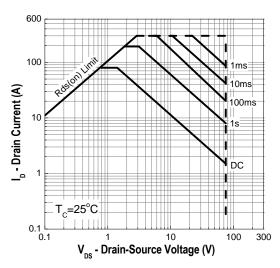
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Typical Operating Characteristics (Cont.)

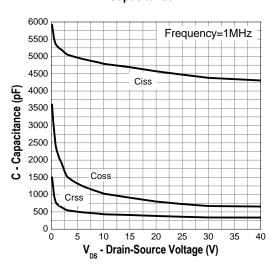
Power Dissipation



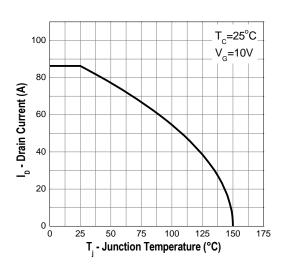
Safe Operation Area



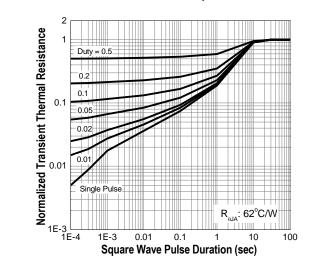
Capacitance



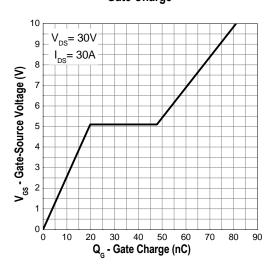
Drain Current



Transient Thermal Impedance



Gate Charge





SG75N07PB 80V N-Channel Power MOSFET

Marking Information

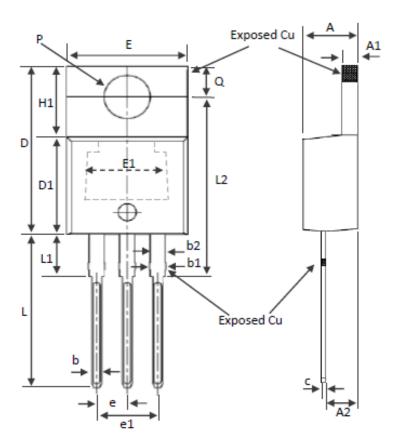
TO-220A	AB-D (PB)	Marking Rule
YY	75N07PB YMMXXX Diagram	Line 1 : Device SG75N07PB Line 2 : Date Code YYMMXXX YY : Year Code MM : Month Code XXX : Serial Number



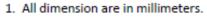


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Package of Dimension



Symbol	Min	Nor	Max
Α	3.56	4.57	4.82
A1	0.51	1.27	1.39
A2	2.04	2.67	2.92
b	0.39	0.81	1.01
b1	1.15	1.37	1.82
b2	1.15	1.27	1.77
D	14.22	15.00	16.51
D1	8.39	8.70	9.01
D2	11.45	11.94	12.87
E	9.66	10.11	10.66
E1	6.86	7.00	8.89
e		2.54 Ref.	
e1		5.08 Ref.	
H1	5.85	6.30	6.85
L	12.70	13.60	14.73
L1	-	3.75	6.35
L2	15.80	16.00	16.20
Р	3.54	3.87	4.08
Q	2.54	2.74	3.42



2. Dimension does not include burrs and mold flash/protrusions.

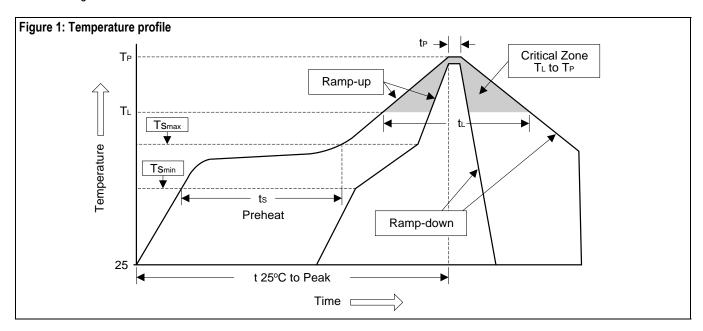




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Soldering Methods for Silicongear's Products

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T _L to T _P)	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts _{min})	100°C	150°C
- Temperature Max (Ts _{max})	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t∟)	60 to 150 sec	60 to 150 sec
Peak Temperature (T _P)	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t₂)	10 to 50 sec	20 to 40 Sec
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec



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